REMARKS

Applicant respectfully requests reconsideration of the present application in view of the foregoing amendments and in view of the reasons that follow.

Claims 1-6 were pending at the time of the outstanding Office Action. By way of the instant amendment, claim 4 has been cancelled and claims 7-18 have been added. Thus, claims 1-3 and 5-18 remain for examination.

The Examiner has indicated that claims 4-6 are objected to as dependent from a rejected base claim but would otherwise be allowable if written in independent form.

By way of the instant amendment, the recitations of claim 4 have been incorporated into independent claim 1, and claim 4 has been cancelled. Thus, it is submitted that claim 1 is in condition for allowance. Moreover, claims 2, 3, 5 and 6 depending directly or indirectly upon claim 1 and are thus likewise deemed allowable.

New claim 7 has been added which includes the subject matter of original claim 4 but deletes the last paragraph of original claim 1. It would appear that the Examiner's indication of allowability is based on the recitations of dependent claim 4 and, indeed, the last paragraph of original claim 1 was deemed to be disclosed by the Yamazaki patent. Thus, deletion of this paragraph is not deemed to change the essential reasons for allowability of the subject matter of applicant's original claim 4. Thus, it is submitted that claim 7 is likewise allowable. Claims 8-11, parallel claims 2, 3, 5 and 6, respectively, depend from newly submitted claim 7 and are thus likewise deemed to be allowable.

Claim 12 is directed toward the ordered sequence of processes shown in applicant's Fig. 1A-1C. Thus, in claim 12, the first dopant is introduced through a protective film (film 4, for example), masking takes place (resist film 5) to delineates first and second transistor regions to be formed on the non-single crystal semiconductor film, the second dopant, of opposite conductivity type to the first dopant, is introduced into the non-single crystal semiconductor film and the second dopant is introduced in regions of the non-single crystal semiconductor film that are exposed by openings in the mask. Subsequently, applicant's newly-submitted claim 12 recites removing the mask and irradiating the non-single crystal semiconductor film with a laser beam to convert a non-single crystal material of the non-single crystal semiconductor film into a single crystal material resulting in formation of a crystallized semiconductor film. Finally, applicant's last step recites forming transistors of

the first and second conductivity types on the crystallized semiconductor film. Inasmuch as claim 12 recites introducing the first dopant through the protective film and recites masking of the surface of the non-single crystal semiconductor film and introducing the second dopant through the mask, removing the mask and the protective film, and irradiating the non-single crystal semiconductor film to form the crystallized semiconductor film, it is submitted that such recitations are consistent with the subject matter of original claim 4 and, thus, claim 12 should likewise be in condition for allowance.

Claim 13 is dependent on claim 12 and adds the subject matter of the last paragraph of original claim 1. Claim 13 is thus likewise deemed to be in condition for allowance.

New claim 14 is similar to claim 12 but omits the step of introducing the first dopant through the protective film. Thus, under conditions where the silicon layer is free from contamination, the protective silicon film 4 is not required as disclosed in applicant's specification on page 9, lines 7-12. However, claim 14 does recite the mask through which the second dopant is introduced and removing the mask prior to the irradiating step. Thus, it is submitted that claim 14 is likewise patentable.

Claim 15 adds the subject matter of the last paragraph of original claim 1 into claim 14 and is likewise deemed patentable.

Newly submitted claim 16 is directed to the sequential process steps shown in applicant's Figs. 3A-3C. In this claim the first dopant is introduced through the protective film, the protective film is removed, the laser beam is irradiated, a mask is applied subsequently to the irradiation, the second dopant is introduced through openings in the mask and subsequently the transistors are formed. It is submitted that claim 16 in reciting the use of the protective film during the introduction of the first dopant and the subsequent removal of the protective film is consistent with the recitations of original independent claim 4 and is thus patentable essentially for the same reasons applicable to claim 4.

New claims 17 and 18 depend on claim 16 and are likewise deemed patentable.

In view of the amendments made hereto and the remarks set forth above, it is submitted that the application is now in condition for allowance and an early indication of same is earnestly solicited.

The Examiner is invited to contact the undersigned by telephone if it is felt that a telephone interview would advance the prosecution of the present application.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741. If any extensions of time are needed for timely acceptance of papers submitted herewith, Applicant hereby petitions for such extension under 37 C.F.R. §1.136 and authorizes payment of any such extensions fees to Deposit Account No. 19-0741.

Respectfully submitted,

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